

TECHNICAL DATA

NPN SILICON MEDIUM POWER TRANSISTOR

Qualified per MIL-PRF-19500/207

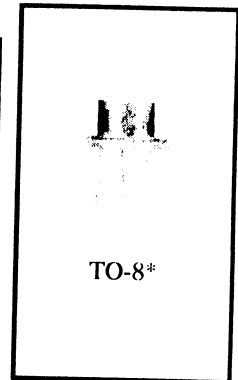
Devices

2N1483 2N1484 2N1485 2N1486

MAXIMUM RATINGS

Ratings	Symbol	2N1483 2N1485	2N1484 2N1486	Unit
Collector-Emitter Voltage	V_{CE0}	40	55	Vdc
Collector-Base Voltage	V_{CBO}	60	100	Vdc
Emitter-Base Voltage	V_{EBO}	12		Vdc
Collector Current -- Continuous	I_C	3.0		Adc
Total Power Dissipation	P_T	@ $T_A = 25^{\circ}C^{(1)}$	1.75	W
		@ $T_C = 25^{\circ}C^{(2)}$	25	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

- 1) Derate linearly 0.010 W/ $^{\circ}C$ for $T_A > 25^{\circ}C$
2) Derate linearly 0.143 W/ $^{\circ}C$ for $T_C > 25^{\circ}C$



*See Appendix A for Package Outline

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_C = 100 \text{ mAdc}$	$V_{(BR)CEO}$	40 55		Vdc
Collector-Base Breakdown Voltage $I_C = 100 \mu\text{Adc}$	$V_{(BR)CBO}$	60 100		Vdc
Collector-Emitter Breakdown Voltage $V_{IB} = 1.5 \text{ Vdc}, I_C = 0.25 \text{ mAdc}$	$V_{(BR)CEX}$	60 100		Vdc
Collector-Base Cutoff Current $V_{CB} = 30 \text{ Vdc}$ $V_{CB} = 50 \text{ Vdc}$	I_{CBO}		15 15	μAdc
Emitter-Base Cutoff Current $V_{EB} = 12 \text{ Vdc}$	I_{EBO}		15	μAdc

